Lattice Semiconductor Corporation - LFE5U-25F-6BG256I Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	6000
Number of Logic Elements/Cells	24000
Total RAM Bits	1032192
Number of I/O	197
Number of Gates	-
Voltage - Supply	1.045V ~ 1.155V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	256-LFBGA
Supplier Device Package	256-CABGA (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe5u-25f-6bg256i

Figures

Tables

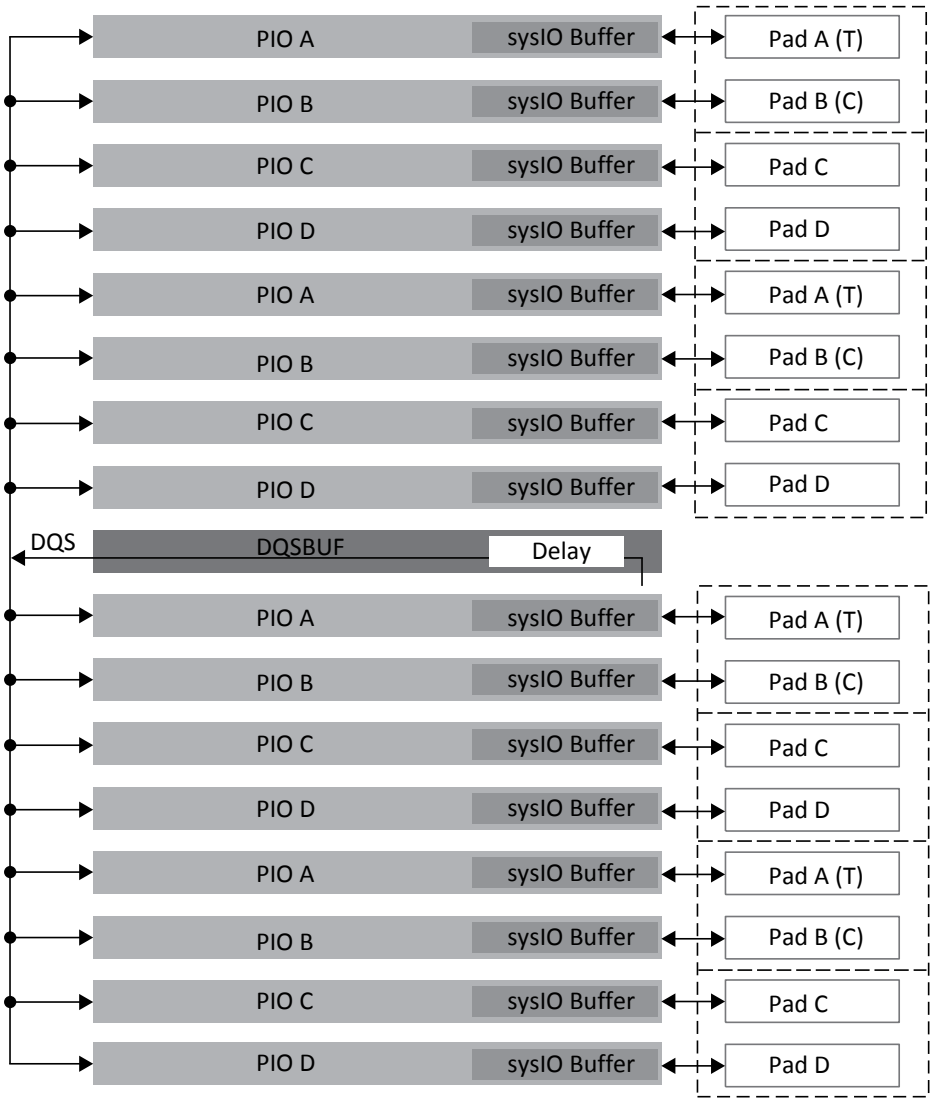


Figure 2.23. DQS Grouping on the Left and Right Edges

2.13.2. DLL Calibrated DQS Delay and Control Block (DQSBUF)

To support DDR memory interfaces (DDR2/3, LPDDR2/3), the DQS strobe signal from the memory must be used to capture the data (DQ) in the PIC registers during memory reads. This signal is output from the DDR memory device aligned to data transitions and must be time shifted before it can be used to capture data in the PIC. This time shifted is achieved by using DQSDEL programmable delay line in the DQS Delay Block (DQS read circuit). The DQSDEL is implemented as a slave delay line and works in conjunction with a master DDRDLL.

This block also includes slave delay line to generate delayed clocks used in the write side to generate DQ and DQS with correct phases within one DQS group. There is a third delay line inside this block used to provide write leveling feature for DDR write if needed.

Each of the read and write side delays can be dynamically shifted using margin control signals that can be controlled by the core logic.

FIFO Control Block shown in Figure 2.24 generates the Read and Write Pointers for the FIFO block inside the Input Register Block. These pointers are generated to control the DQS to ECLK domain crossing using the FIFO module.

2.14. sysI/O Buffer

Each I/O is associated with a flexible buffer referred to as a sysI/O buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysI/O buffers allow users to implement the wide variety of standards that are found in today's systems including LVDS, HSUL, BLVDS, SSTL Class I and II, LVCMOS, LVTTL, LVPECL, and MIPI.

2.14.1. sysI/O Buffer Banks

ECP5/ECP5-5G devices have seven sysI/O buffer banks, two banks per side at Top, Left and Right, plus one at the bottom left side. The bottom left side bank (Bank 8) is a shared I/O bank. The I/Os in that bank contains both dedicated and shared I/O for sysConfig function. When a shared pin is not used for configuration, it is available as a user I/O. For LFE5-85 devices, there is an additional I/O bank (Bank 4) that is not available in other device in the family.

In ECP5/ECP5-5G devices, the Left and Right sides are tailored to support high performance interfaces, such as DDR2, DDR3, LPDDR2, LPDDR3 and other high speed source synchronous standards. The banks on the Left and Right sides of the devices feature LVDS input and output buffers, data-width gearing, and DQSBUF block to support DDR2/3 and LPDDR2/3 interfaces. The I/Os on the top and bottom banks do not have LVDS input and output buffer, and gearing logic, but can use LVCMOS to emulate most of differential output signaling.

Each sysIO bank has its own I/O supply voltage (V_{CCIO}). In addition, the banks on the Left and Right sides of the device, have voltage reference input (shared I/O pin), VREF1 per bank, which allow it to be completely independent of each other. The V_{REF} voltage is used to set the threshold for the referenced input buffers, such as SSTL. Figure 2.25 shows the seven banks and their associated supplies.

In ECP5/ECP5-5G devices, single-ended output buffers and ratioed input buffers (LVTTL, and LVCMOS) are powered using V_{CCIO}. LVTTL, LVCMOS33, LVCMOS25 and LVCMOS12 can also be set as fixed threshold inputs independent of V_{CCIO}.

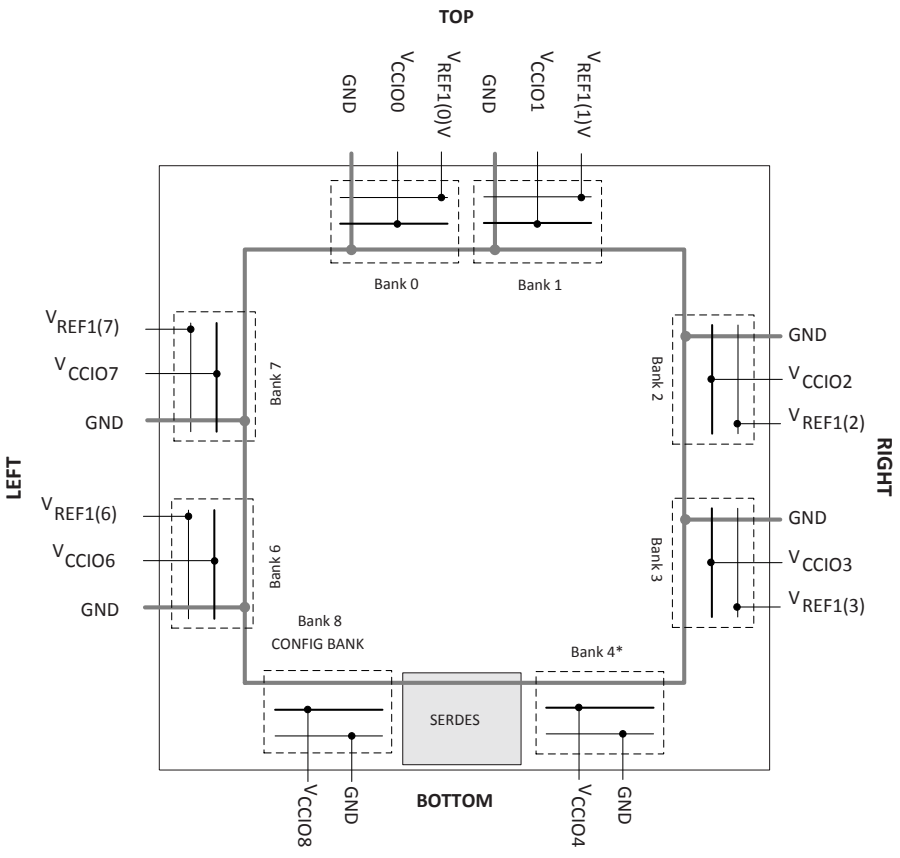


Figure 2.25. ECP5/ECP5-5G Device Family Banks

2.14.4. On-Chip Programmable Termination

The ECP5/ECP5-5G devices support a variety of programmable on-chip terminations options, including:

- Dynamically switchable Single-Ended Termination with programmable resistor values of 50 Ω, 75 Ω, or 150 Ω.
- Common mode termination of 100 Ω for differential inputs.

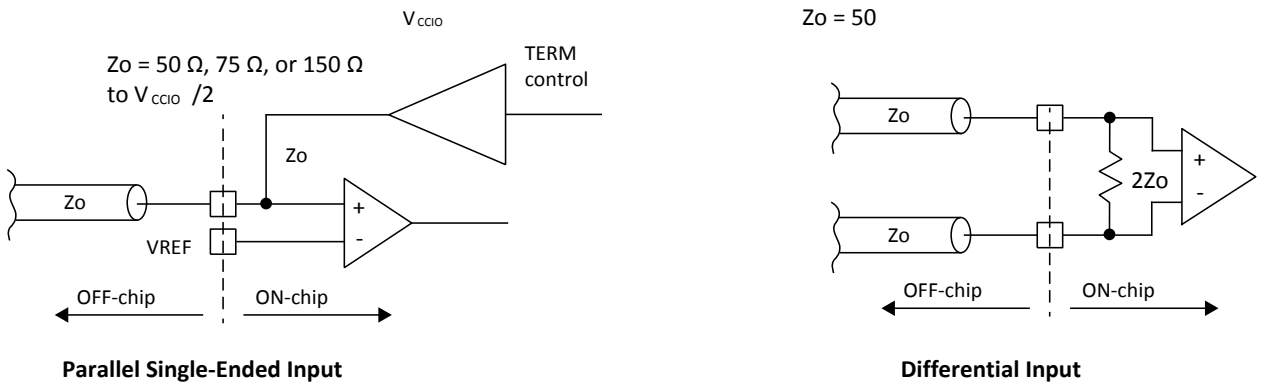


Figure 2.26. On-Chip Termination

See Table 2.12 for termination options for input modes.

Table 2.12. On-Chip Termination Options for Input Modes

IO_TYPE	Terminate to $V_{CCIO}/2$*	Differential Termination Resistor*
LVDS25	—	100
BLVDS25	—	100
MLVDS	—	100
LVPECL33	—	100
subLVDS	—	100
SLVS	—	100
HSUL12	50, 75, 150	—
HSUL12D	—	100
SSTL135_I / II	50, 75, 150	—
SSTL135D_I / II	—	100
SSTL15_I / II	50, 75, 150	—
SSTL15D_I / II	—	100
SSTL18_I / II	50, 75, 150	—
SSTL18D_I / II	—	100

***Notes**:

TERMINATE to $V_{CCIO}/2$ (Single-Ended) and DIFFRENTIAL TERMINATION RESISTOR when turned on can only have one setting per bank. Only left and right banks have this feature.

Use of TERMINATE to $V_{CCIO}/2$ and DIFFRENTIAL TERMINATION RESISTOR are mutually exclusive in an I/O bank. On-chip termination tolerance ±20%.

Refer to ECP5 and ECP5-5G sysIO Usage Guide (TN1262) for on-chip termination usage and value ranges.

2.14.5. Hot Socketing

ECP5/ECP5-5G devices have been carefully designed to ensure predictable behavior during power-up and power-down. During power-up and power-down sequences, the I/Os remain in tristate until the power supply voltage is high enough to ensure reliable operation. In addition, leakage into I/O pins is controlled within specified limits. See the Hot Socketing Specifications section on page 48.

3. DC and Switching Characteristics

3.1. Absolute Maximum Ratings

Table 3.1. Absolute Maximum Ratings

Symbol	Parameter	Min	Max	Unit
V_{CC}	Supply Voltage	–0.5	1.32	V
V_{CCA}	Supply Voltage	–0.5	1.32	V
V_{CCAUX}, V_{CCAUXA}	Supply Voltage	–0.5	2.75	V
V_{CCIO}	Supply Voltage	–0.5	3.63	V
—	Input or I/O Transient Voltage Applied	–0.5	3.63	V
V_{CCHRX}, V_{CCHTX}	SERDES RX/TX Buffer Supply Voltages	–0.5	1.32	V
—	Voltage Applied on SERDES Pins	–0.5	1.80	V
T_A	Storage Temperature (Ambient)	–65	150	°C
T_J	Junction Temperature	—	+125	°C

Notes:
1. Stress above those listed under the “Absolute Maximum Ratings” may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.
2. Compliance with the Lattice Thermal Management document is required.
3. All voltages referenced to GND.

3.2. Recommended Operating Conditions

Table 3.2. Recommended Operating Conditions

Symbol	Parameter		Min	Max	Unit
V_{CC}[2]	Core Supply Voltage	ECP5	1.045	1.155	V
		ECP5-5G	1.14	1.26	V
V_{CCAUX}[2, 4]	Auxiliary Supply Voltage	—	2.375	2.625	V
V_{CCIO}[2, 3]	I/O Driver Supply Voltage	—	1.14	3.465	V
V_{REF}[1]	Input Reference Voltage	—	0.5	1.0	V
t_{JCOM}	Junction Temperature, Commercial Operation	—	0	85	°C
t_{JIND}	Junction Temperature, Industrial Operation	—	–40	100	°C
SERDES External Power Supply[5]					
V_{CCA}	SERDES Analog Power Supply	ECP5UM	1.045	1.155	V
		ECP5-5G	1.164	1.236	V
V_{CCAUXA}	SERDES Auxiliary Supply Voltage	—	2.374	2.625	V
V_{CCHRX}[6]	SERDES Input Buffer Power Supply	ECP5UM	0.30	1.155	V
		ECP5-5G	0.30	1.26	V
V_{CCHTX}	SERDES Output Buffer Power Supply	ECP5UM	1.045	1.155	V
		ECP5-5G	1.14	1.26	V

Notes:
1. For correct operation, all supplies except V_{REF} must be held in their valid operation range. This is true independent of feature usage.
2. All supplies with same voltage, except SERDES Power Supplies, should be connected together.
3. See recommended voltages by I/O standard in Table 3.4 on page 48.
4. V_{CCAUX} ramp rate must not exceed 30 mV/µs during power-up when transitioning between 0 V and 3 V.
5. Refer to ECP5 and ECP5-5G SERDES/PCS Usage Guide (TN1261) for information on board considerations for SERDES power supplies.
6. V_{CCHRX} is used for Rx termination. It can be biased to Vcm if external AC coupling is used. This voltage needs to meet all the HDin input voltage level requirements specified in the Rx section of this Data Sheet.

3.7. Hot Socketing Requirements

Table 3.6. Hot Socketing Requirements

Description	Min	Typ	Max	Unit
Input current per SERDES I/O pin when device is powered down and inputs driven.	—	—	8	mA
Input current per HDIN pin when device power supply is off, inputs driven[1, 2]	—	—	15	mA
Current per HDIN pin when device power ramps up, input driven[3]	—	—	50	mA
Current per HDOUT pin when device power supply is off, outputs pulled up[4]	—	—	30	mA

Notes:

1. Device is powered down with all supplies grounded, both HDINP and HDINN inputs driven by a CML driver with maximum allowed output V_{CCHTX}, 8b/10b data, no external AC coupling.
2. Each P and N input must have less than the specified maximum input current during hot plug. For a device with 2 DCU, the total input current would be 15 mA * 4 channels * 2 input pins per channel = 120 mA.
3. Device power supplies are ramping up (V_{CCA} and V_{CCAUX}), both HDINP and HDINN inputs are driven by a CML driver with maximum allowed output V_{CCHTX}, 8b/10b data, internal AC coupling.
4. Device is powered down with all supplies grounded. Both HDOUTP and HDOUN outputs are pulled up to V_{CCHTX} by the far end receiver termination of 50 Ω single ended.

3.8. ESD Performance

Refer to the ECP5 and ECP5-5G Product Family Qualification Summary for complete qualification data, including ESD performance.

3.9. DC Electrical Characteristics

Over Recommended Operating Conditions

Table 3.7. DC Electrical Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IL}, I_{IH}[1, 4]	Input or I/O Low Leakage	$0 \le V_{IN} \le V_{CCIO}$	—	—	10	µA
I_{IH}[1, 3]	Input or I/O High Leakage	$V_{CCIO} < V_{IN} \le V_{IH(MAX)}$	—	—	100	µA
I_{PU}	I/O Active Pull-up Current, sustaining logic HIGH state	$0.7\ V_{CCIO} \le V_{IN} \le V_{CCIO}$	–30	—	—	µA
	I/O Active Pull-up Current, pulling down from logic HIGH state	$0 \le V_{IN} \le 0.7\ V_{CCIO}$	—	—	–150	µA
I_{PD}	I/O Active Pull-down Current, sustaining logic LOW state	$0 \le V_{IN} \le V_{IL}$ (MAX)	30	—	—	µA
	I/O Active Pull-down Current, pulling up from logic LOW state	$0 \le V_{IN} \le V_{CCIO}$	—	—	150	µA
C1	I/O Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = 1.2 V, V_{IO} = 0 to $V_{IH(MAX)}$	—	5	8	pf
C2	Dedicated Input Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = 1.2 V, V_{IO} = 0 to $V_{IH(MAX)}$	—	5	7	pf
V_{HYST}	Hysteresis for Single-Ended Inputs	V_{CCIO} = 3.3 V	—	300	—	mV
		V_{CCIO} = 2.5 V	—	250	—	mV

Notes:

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tristated. It is not measured with the output driver active. Bus maintenance circuits are disabled.
2. T_A 25 °C, f = 1.0 MHz.
3. Applicable to general purpose I/Os in top and bottom banks.
4. When used as V_{REF}, maximum leakage= 25 µA.

3.13. sysI/O Single-Ended DC Electrical Characteristics

Table 3.12. Single-Ended DC Characteristics

Input/Output Standard	V_{IL}		V_{IH}		V_{OL} Max (V)	V_{OH} Min (V)	I_{OL}[1] (mA)	I_{OH}[1] (mA)
	Min (V)	Max (V)	Min (V)	Max (V)				
LVCMOS33	–0.3	0.8	2.0	3.465	0.4	V_{CCIO} – 0.4	16, 12, 8, 4	–16, –12, –8, –4
LVCMOS25	–0.3	0.7	1.7	3.465	0.4	V_{CCIO} – 0.4	12, 8, 4	–12, –8, –4
LVCMOS18	–0.3	0.35 V_{CCIO}	0.65 V_{CCIO}	3.465	0.4	V_{CCIO} – 0.4	12, 8, 4	–12, –8, –4
LVCMOS15	–0.3	0.35 V_{CCIO}	0.65 V_{CCIO}	3.465	0.4	V_{CCIO} – 0.4	8, 4	–8, –4
LVCMOS12	–0.3	0.35 V_{CCIO}	0.65 V_{CCIO}	3.465	0.4	V_{CCIO} – 0.4	8, 4	–8, –4
LVTTL33	–0.3	0.8	2.0	3.465	0.4	V_{CCIO} – 0.4	16, 12, 8, 4	–16, –12, –8, –4
SSTL18_I (DDR2 Memory)	–0.3	V_{REF} – 0.125	V_{REF} + 0.125	3.465	0.4	V_{CCIO} – 0.4	6.7	–6.7
SSTL18_II	–0.3	V_{REF} –	V_{REF} + 0.125	3.465	0.28	V_{CCIO} – 0.28	13.4	–13.4
SSTL15 _I (DDR3 Memory)	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.465	0.31	V_{CCIO} – 0.31	7.5	–7.5
SSTL15_II (DDR3 Memory)	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.465	0.31	V_{CCIO} – 0.31	8.8	–8.8
SSTL135_I (DDR3L Memory)	–0.3	V_{REF} – 0.09	V_{REF} + 0.09	3.465	0.27	V_{CCIO} – 0.27	7	–7
SSTL135_II (DDR3L Memory)	–0.3	V_{REF} – 0.09	V_{REF} + 0.09	3.465	0.27	V_{CCIO} – 0.27	8	–8
MIPI D-PHY (LP)[3]	–0.3	0.55	0.88	3.465	—	—	—	—
HSUL12 (LPDDR2/3 Memory)	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.465	0.3	V_{CCIO} – 0.3	4	–4

Notes:

1. For electromigration, the average DC current drawn by the I/O pads within a bank of I/Os shall not exceed 10 mA per I/O (All I/Os used in the same V_{CCIO}).
2. Not all IO types are supported in all banks. Refer to ECP5 and ECP5-5G sysIO Usage Guide (TN1262) for details.
3. MIPI D-PHY LP input can be implemented by powering VCCIO to 1.5V, and select MIPI LP primitive to meet MIPI Alliance spec on V_{IH} and V_{IL}. It can also be implemented as LVCMOS12 with VCCIO at 1.2V, which would meet V_{IH}/V_{IL} spec on LVCOM12.

3.14.4. LVDS25E

The top and bottom sides of ECP5/ECP5-5G devices support LVDS outputs via emulated complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The scheme shown in Figure 3.1 is one possible solution for point-to-point signals.

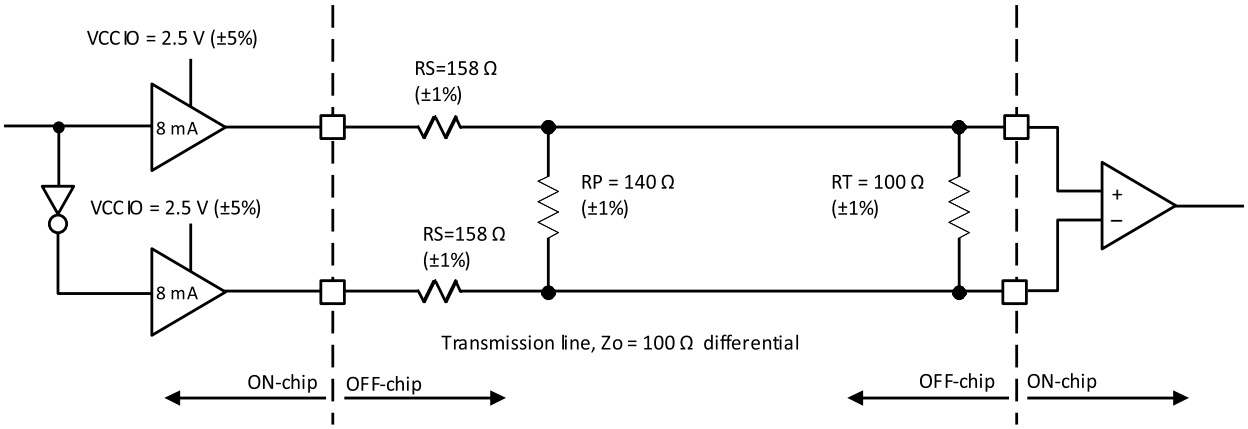


Figure 3.1. LVDS25E Output Termination Example

Table 3.14. LVDS25E DC Conditions

Parameter	Description	Typical	Unit
V_{CCIO}	Output Driver Supply (±5%)	2.50	V
Z_{OUT}	Driver Impedance	20	Ω
R_S	Driver Series Resistor (±1%)	158	Ω
R_P	Driver Parallel Resistor (±1%)	140	Ω
R_T	Receiver Termination (±1%)	100	Ω
V_{OH}	Output High Voltage	1.43	V
V_{OL}	Output Low Voltage	1.07	V
V_{OD}	Output Differential Voltage	0.35	V
V_{CM}	Output Common Mode Voltage	1.25	V
Z_{BACK}	Back Impedance	100.5	Ω
I_{DC}	DC Output Current	6.03	mA

Note: For input buffer, see LVDS Table 3.13 on page 55.

Parameter	Description	Device	–8		–7		–6		Unit
			Min	Max	Min	Max	Min	Max	
f_{DATA_DDR2} f_{DATA_DDR3} f_{DATA_DDR3L} f_{DATA_LPDDR2} f_{DATA_LPDDR3}	DDR Memory Data Rate	All Devices	—	800	—	700	—	624	Mb/s
f_{MAX_DDR2} f_{MAX_DDR3} f_{MAX_DDR3L} f_{MAX_LPDDR2} f_{MAX_LPDDR3}	DDR Memory CLK Frequency (ECLK)	All Devices	—	400	—	350	—	312	MHz
DDR2/DDR3/DDR3L/LPDDR2/LPDDR3 WRITE (DQ Output Data are Centered to DQS)									
t_{DQVBS_DDR2} t_{DQVBS_DDR3} t_{DQVBS_DDR3L} t_{DQVBS_LPDDR2} t_{DQVBS_LPDDR3}	Data Output Valid before DQS Output	All Devices	—	–0.25	—	–0.25	—	-0.25	UI
t_{DQVAS_DDR2} t_{DQVAS_DDR3} t_{DQVAS_DDR3L} t_{DQVAS_LPDDR2} t_{DQVAS_LPDDR3}	Data Output Valid after DQS Output	All Devices	0.25	—	0.25	—	0.25	—	UI
f_{DATA_DDR2} f_{DATA_DDR3} f_{DATA_DDR3L} f_{DATA_LPDDR2} f_{DATA_LPDDR3}	DDR Memory Data Rate	All Devices	—	800	—	700	—	624	Mb/s
f_{MAX_DDR2} f_{MAX_DDR3} f_{MAX_DDR3L} f_{MAX_LPDDR2} f_{MAX_LPDDR3}	DDR Memory CLK Frequency (ECLK)	All Devices	—	400	—	350	—	312	MHz

Notes:

1. Commercial timing numbers are shown. Industrial numbers are typically slower and can be extracted from the Diamond software.
2. General I/O timing numbers are based on LVCMOS 2.5, 12 mA, Fast Slew Rate, 0pf load.
   Generic DDR timing are numbers based on LVDS I/O.
   DDR2 timing numbers are based on SSTL18.
   DDR3 timing numbers are based on SSTL15.
   LPDDR2 and LPDDR3 timing numbers are based on HSUL12.
3. Uses LVDS I/O standard for measurements.
4. Maximum clock frequencies are tested under best case conditions. System performance may vary upon the user environment.
5. All numbers are generated with the Diamond software.

3.21. SERDES/PCS Block Latency

Table 3.26 describes the latency of each functional block in the transmitter and receiver. Latency is given in parallel clock cycles. Figure 3.13 shows the location of each block.

Table 3.26. SERDES/PCS Latency Breakdown

Item	Description	Min	Avg	Max	Fixed	Bypass	Unit[3]
Transmit Data Latency[1]							
T1	FPGA Bridge - Gearing disabled with same clocks	3	—	4	—	1	byte clk
	FPGA Bridge - Gearing enabled	5	—	7	—	—	word clk
T2	8b10b Encoder	—	—	—	2	1	byte clk
T3	SERDES Bridge transmit	—	—	—	2	1	byte clk
T4	Serializer: 8-bit mode	—	—	—	15 + Δ1	—	UI + ps
	Serializer: 10-bit mode	—	—	—	18 + Δ1	—	UI + ps
T5	Pre-emphasis ON	—	—	—	1 + Δ2	—	UI + ps
	Pre-emphasis OFF	—	—	—	0 + Δ3	—	UI + ps
Receive Data Latency[2]							
R1	Equalization ON	—	—	—	Δ1	—	UI + ps
	Equalization OFF	—	—	—	Δ2	—	UI + ps
R2	Deserializer: 8-bit mode	—	—	—	10 + Δ3	—	UI + ps
	Deserializer: 10-bit mode	—	—	—	12 + Δ3	—	UI + ps
R3	SERDES Bridge receive	—	—	—	2	—	byte clk
R4	Word alignment	3.1	—	4	—	1	byte clk
R5	8b10b decoder	—	—	—	1	0	byte clk
R6	Clock Tolerance Compensation	7	15	23	—	1	byte clk
R7	FPGA Bridge - Gearing disabled with same clocks	4	—	5	—	1	byte clk
	FPGA Bridge - Gearing enabled	7	—	9	—	—	word clk

Notes:

1. Δ1 = –245 ps, Δ2 = +88 ps, Δ3 = +112 ps.
2. Δ1 = +118 ps, Δ2 = +132 ps, Δ3 = +700 ps.
3. byte clk = 8UIs (8-bit mode), or 10 UIs (10-bit mode); word clk = 16UIs (8-bit mode), or 20 UIs (10-bit mode).

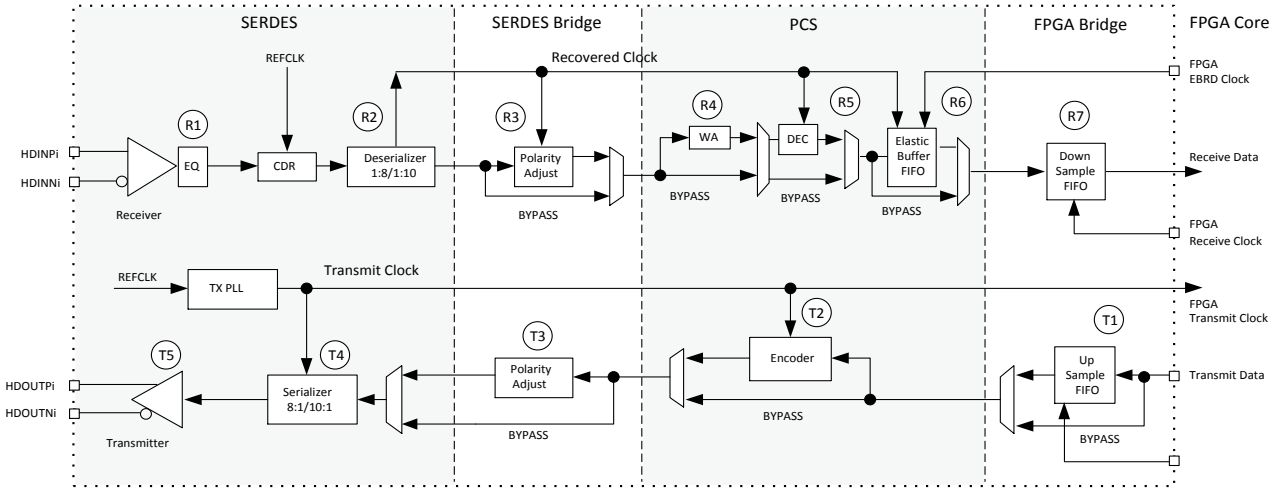


Figure 3.13. Transmitter and Receiver Latency Block Diagram

3.22. SERDES High-Speed Data Receiver

Table 3.27. Serial Input Data Specifications

Symbol	Description	Min	Typ	Max	Unit
$V_{RX-DIFF-S}$	Differential input sensitivity	150	—	1760	mV, p-p
V_{RX-IN}	Input levels	0	—	V_{CCA} +0.5[2]	V
$V_{RX-CM-DCCM}$	Input common mode range (internal DC coupled mode)	0.6	—	V_{CCA}	V
$V_{RX-CM-ACCM}$	Input common mode range (internal AC coupled mode)[2]	0.1	—	V_{CCA} +0.2	V
$T_{RX-RELOCK}$	SCDR re-lock time[1]	—	1000	—	Bits
$Z_{RX-TERM}$	Input termination 50/75 Ω /High Z	–20%	50/75/5 K	+20%	Ω
RL_{RX-RL}	Return loss (without package)	—	—	–10	dB

Notes:
1. This is the typical number of bit times to re-lock to a new phase or frequency within ±300 ppm, assuming 8b10b encoded data.
2. Up to 1.655 for ECP5, and 1.76 for ECP5-5G.

3.23. Input Data Jitter Tolerance

A receiver's ability to tolerate incoming signal jitter is very dependent on jitter type. High speed serial interface standards have recognized the dependency on jitter type and have specifications to indicate tolerance levels for different jitter types as they relate to specific protocols. Sinusoidal jitter is considered to be a worst case jitter type.

Table 3.28. Receiver Total Jitter Tolerance Specification

Description	Frequency	Condition	Min	Typ	Max	Unit
Deterministic	5 Gb/s	400 mV differential eye	—	—	TBD	UI, p-p
Random		400 mV differential eye	—	—	TBD	UI, p-p
Total		400 mV differential eye	—	—	TBD	UI, p-p
Deterministic	3.125 Gb/s	400 mV differential eye	—	—	0.37	UI, p-p
Random		400 mV differential eye	—	—	0.18	UI, p-p
Total		400 mV differential eye	—	—	0.65	UI, p-p
Deterministic	2.5 Gb/s	400 mV differential eye	—	—	0.37	UI, p-p
Random		400 mV differential eye	—	—	0.18	UI, p-p
Total		400 mV differential eye	—	—	0.65	UI, p-p
Deterministic	1.25 Gb/s	400 mV differential eye	—	—	0.37	UI, p-p
Random		400 mV differential eye	—	—	0.18	UI, p-p
Total		400 mV differential eye	—	—	0.65	UI, p-p

Notes:
1. Jitter tolerance measurements are done with protocol compliance tests: 3.125 Gb/s - XAUI Standard, 2.5 Gb/s - PCIe Standard, 1.25 Gb/s - SGMII Standard.
2. For ECP5-5G family devices only.

Table 3.31. PCIe (5 Gb/s) *(Continued)*

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
Receive[1, 2]						
UI	Unit Interval	—	199.94	200	200.06	ps
$V_{RX-DIFF-PP}$	Differential Rx peak-peak voltage	—	0.34[3]	—	1.2	V, p-p
$T_{RX-RJ-RMS}$	Receiver random jitter tolerance (RMS)	1.5 MHz – 100 MHz Random noise	—	—	4.2	ps, RMS
T_{RX-DJ}	Receiver deterministic jitter tolerance	—	—	—	88	ps
$V_{RX-CM-AC}$	Common mode noise from Rx	—	—	—		mV, p-p
$R_{LRX-DIFF}$	Receiver differential Return Loss, package plus silicon	50 MHz < freq < 1.25 GHz	10	—	—	dB
		1.25 GHz < freq < 2.5 GHz	8	—	—	dB
R_{LRX-CM}	Receiver common mode Return Loss, package plus silicon	—	6	—	—	dB
Z_{RX-DC}	Receiver DC single ended impedance	—	40	—	60	Ω
$Z_{RX-HIGH-IMP-DC}$	Receiver DC single ended impedance when powered down	—	200K	—	—	Ω
$V_{RX-CM-AC-P}$	Rx AC peak common mode voltage	—	—	—		mV, peak
$V_{RX-IDLE-DET-DIFF-PP}$	Electrical Idle Detect Threshold	—	65	—	340[3]	mv,
$L_{RX-SKEW}$	Receiver lane-lane skew	—	—	—	8	ns

Notes:

1. Values are measured at 5 Gb/s.
2. Measured with external AC-coupling on the receiver.
3. Not in compliance with PCI Express standard.

4.2. PICs and DDR Data (DQ) Pins Associated with the DDR Strobe (DQS) Pin

PICs Associated with DQS Strobe	PIO within PIC	DDR Strobe (DQS) and Data (DQ) Pins
For Left and Right Edges of the Device Only		
P[L/R] [n–6]	A	DQ
	B	DQ
	C	DQ
	D	DQ
P[L/R] [n–3]	A	DQ
	B	DQ
	C	DQ
	D	DQ
P[L/R] [n]	A	DQS (P)
	B	DQS (N)
	C	DQ
	D	DQ
P[L/R] [n+3]	A	DQ
	B	DQ
	C	DQ
	D	DQ

Note: "n" is a row PIC number.

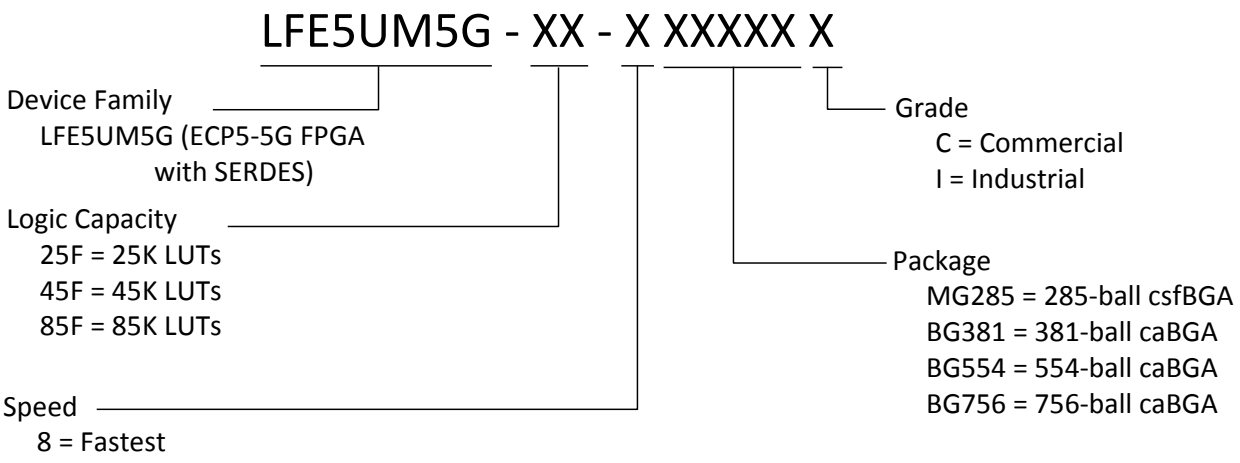
4.3. Pin Information Summary

4.3.1. LFE5UM/LFE5UM5G

Pin Information Summary		LFE5UM/ LFE5UM5G-25		LFE5UM/LFE5UM5G-45			LFE5UM/LFE5UM5G-85			
Pin Type		285 csfBG	381 caBGA	285 csfBGA	381 caBG	554 caBGA	285 csfBGA	381 caBG	554 caBGA	756 caBGA
General Purpose Inputs/Outputs per Bank	Bank 0	6	24	6	27	32	6	27	32	56
	Bank 1	6	32	6	33	40	6	33	40	48
	Bank 2	21	32	21	32	32	21	34	32	48
	Bank 3	28	32	28	33	48	28	33	48	64
	Bank 4	0	0	0	0	0	0	0	14	24
	Bank 6	26	32	26	33	48	26	33	48	64
	Bank 7	18	32	18	32	32	18	32	32	48
	Bank 8	13	13	13	13	13	13	13	13	13
Total Single-Ended User I/O		118	197	118	203	245	118	205	259	365
VCC		13	20	13	20	24	13	20	24	36
VCCAUX (Core)		3	4	3	4	9	3	4	9	8
VCCIO	Bank 0	1	2	1	2	3	1	2	3	4
	Bank 1	1	2	1	2	3	1	2	3	4
	Bank 2	2	3	2	3	4	2	3	4	4
	Bank 3	2	3	2	3	3	2	3	3	4
	Bank 4	0	0	0	0	0	0	0	2	2
	Bank 6	2	3	2	3	4	2	3	4	4
	Bank 7	2	3	2	3	3	2	3	3	4
	Bank 8	2	2	2	2	2	2	2	2	2

4.3.2. LFE5U

Pin Information Summary		LFE5U-12			LFE5U-25			LFE5U-45				LFE5U-85			
Pin Type		256 caBGA	285 csfBGA	381 caBGA	256 caBGA	285 csfBGA	381 caBGA	256 caBGA	285 csfBGA	381 caBGA	554 caBGA	285 csfBG	381 caBGA	554 caBGA	756 caBG
General Purpose Inputs/Outputs per Bank	Bank 0	24	6	24	24	6	24	24	6	27	32	6	27	32	56
	Bank 1	32	6	32	32	6	32	32	6	33	40	6	33	40	48
	Bank 2	32	21	32	32	21	32	32	21	32	32	21	34	32	48
	Bank 3	32	28	32	32	28	32	32	28	33	48	28	33	48	64
	Bank 4	0	0	0	0	0	0	0	0	0	0	0	0	14	24
	Bank 6	32	26	32	32	26	32	32	26	33	48	26	33	48	64
	Bank 7	32	18	32	32	18	32	32	18	32	32	18	32	32	48
	Bank 8	13	13	13	13	13	13	13	13	13	13	13	13	13	13
Total Single-Ended User		197	118	197	197	118	197	197	118	203	245	118	205	259	365
VCC		6	13	20	6	13	20	6	13	20	24	13	20	24	36
VCCAUX (Core)		2	3	4	2	3	4	2	3	4	9	3	4	9	8
VCCIO	Bank 0	2	1	2	2	1	2	2	1	2	3	1	2	3	4
	Bank 1	2	1	2	2	1	2	2	1	2	3	1	2	3	4
	Bank 2	2	2	3	2	2	3	2	2	3	4	2	3	4	4
	Bank 3	2	2	3	2	2	3	2	2	3	3	2	3	3	4
	Bank 4	0	0	0	0	0	0	0	0	0	0	0	0	2	2
	Bank 6	2	2	3	2	2	3	2	2	3	4	2	3	4	4
	Bank 7	2	2	3	2	2	3	2	2	3	3	2	3	3	4
	Bank 8	1	2	2	1	2	2	1	2	2	2	2	2	2	2
TAP		4	4	4	4	4	4	4	4	4	4	4	4	4	4
Miscellaneous Dedicated		7	7	7	7	7	7	7	7	7	7	7	7	7	7
GND		27	123	99	27	123	99	27	123	99	198	123	99	198	267
NC		0	1	26	0	1	26	0	1	26	33	1	26	33	29
Reserved		0	4	6	0	4	6	0	4	6	12	4	6	12	12
Total Balls		256	285	381	256	285	381	256	285	381	554	285	381	554	756
High Speed Differential Input / Output Pairs	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank	16/8	10/8	16/8	16/8	10/8	16/8	16/8	10/8	16/8	16/8	10/8	17/9	16/8	
	Bank	16/8	14/7	16/8	16/8	14/7	16/8	16/8	14/7	16/8	24/12	14/7	16/8	24/1	
	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank	16/8	13/6	16/8	16/8	13/6	16/8	16/8	13/6	16/8	24/12	13/6	16/8	24/1	
	Bank	16/8	8/6	16/8	16/8	8/6	16/8	16/8	8/6	16/8	16/8	8/6	16/8	16/8	
	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Total High Speed		64/32	45/27	64/32	64/32	45/27	64/32	64/32	45/27	64/32	80/40	45/27	65/33	80/40	112/
DQS Groups (> 11 pins in group)	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank	2	1	2	2	1	2	2	1	2	2	1	2	2	
	Bank	2	2	2	2	2	2	2	2	2	3	2	2	3	
	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
	Bank	2	2	2	2	2	2	2	2	2	3	2	2	3	
	Bank	2	1	2	2	1	2	2	1	2	2	1	2	2	
	Bank	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Total DQS Groups		8	6	8	8	6	8	8	6	8	10	6	8	10	14



5.2. Ordering Part Numbers

5.2.1. Commercial

Part number	Grade	Package	Pins	Temp.	LUTs (K)	SERDES
LFE5U-12F-6BG256C	–6	Lead free caBGA	256	Commercial	12	No
LFE5U-12F-7BG256C	–7	Lead free caBGA	256	Commercial	12	No
LFE5U-12F-8BG256C	–8	Lead free caBGA	256	Commercial	12	No
LFE5U-12F-6MG285C	–6	Lead free csfBGA	285	Commercial	12	No
LFE5U-12F-7MG285C	–7	Lead free csfBGA	285	Commercial	12	No
LFE5U-12F-8MG285C	–8	Lead free csfBGA	285	Commercial	12	No
LFE5U-12F-6BG381C	–6	Lead free caBGA	381	Commercial	12	No
LFE5U-12F-7BG381C	–7	Lead free caBGA	381	Commercial	12	No
LFE5U-12F-8BG381C	–8	Lead free caBGA	381	Commercial	12	No
LFE5U-25F-6BG256C	–6	Lead free caBGA	256	Commercial	24	No
LFE5U-25F-7BG256C	–7	Lead free caBGA	256	Commercial	24	No
LFE5U-25F-8BG256C	–8	Lead free caBGA	256	Commercial	24	No
LFE5U-25F-6MG285C	–6	Lead free csfBGA	285	Commercial	24	No
LFE5U-25F-7MG285C	–7	Lead free csfBGA	285	Commercial	24	No
LFE5U-25F-8MG285C	–8	Lead free csfBGA	285	Commercial	24	No
LFE5U-25F-6BG381C	–6	Lead free caBGA	381	Commercial	24	No
LFE5U-25F-7BG381C	–7	Lead free caBGA	381	Commercial	24	No
LFE5U-25F-8BG381C	–8	Lead free caBGA	381	Commercial	24	No
LFE5U-45F-6BG256C	–6	Lead free caBGA	256	Commercial	44	No
LFE5U-45F-7BG256C	–7	Lead free caBGA	256	Commercial	44	No
LFE5U-45F-8BG256C	–8	Lead free caBGA	256	Commercial	44	No
LFE5U-45F-6MG285C	–6	Lead free csfBGA	285	Commercial	44	No
LFE5U-45F-7MG285C	–7	Lead free csfBGA	285	Commercial	44	No
LFE5U-45F-8MG285C	–8	Lead free csfBGA	285	Commercial	44	No
LFE5U-45F-6BG381C	–6	Lead free caBGA	381	Commercial	44	No
LFE5U-45F-7BG381C	–7	Lead free caBGA	381	Commercial	44	No
LFE5U-45F-8BG381C	–8	Lead free caBGA	381	Commercial	44	No
LFE5U-45F-6BG554C	–6	Lead free caBGA	554	Commercial	44	No
LFE5U-45F-7BG554C	–7	Lead free caBGA	554	Commercial	44	No

Revision History

Date	Version	Section	Change Summary
March 2018	1.9	All	Updated formatting and page referencing.
		General Description	Updated Table 1.1. ECP5 and ECP5-5G Family Selection Guide. Added caBGA256 package in LFE5U-45.
		Architecture	Added a row for SGMII in Table 2.13. LFE5UM/LFE5UM5G SERDES Standard Support. Updated footnote #1.
		DC and Switching Characteristics	Updated Table 3.2. Recommended Operating Conditions.
			Added 2 rows and updated values in Table 3.7. DC Electrical Characteristics.
			Updated Table 3.8. ECP5/ECP5-5G Supply Current (Standby).
			Updated Table 3.11. sysI/O Recommended Operating Conditions.
			Updated Table 3.12. Single-Ended DC Characteristics.
			Updated Table 3.13. LVDS.
			Updated Table 3.14. LVDS25E DC Conditions.
			Updated Table 3.21. ECP5/ECP5-5G Maximum I/O Buffer Speed.
			Updated Table 3.28. Receiver Total Jitter Tolerance Specification.
			Updated header name of section 3.28 CPRI LV E.24/SGMII(2.5Gbps) Electrical and Timing Characteristics.
			Updated header name of section 3.29 Gigabit Ethernet/SGMII(1.25Gbps)/CPRI LV E.12 Electrical and Timing Characteristics
		Pinout Information	Updated table in section 4.3.2 LFE5U.
		Ordering Information	Added table rows in 5.2.1 Commercial.
			Added table rows in 5.2.2 Industrial.
		Supplemental Information	Updated For Further Information section.
November 2017	1.8	General Description	Updated Table 1.1. ECP5 and ECP5-5G Family Selection Guide. Added caBGA256 package in LFE5U-12 and LFE5U-25.

(Continued)

Date	Version	Section	Change Summary
August 2014	1.2	DC and Switching Characteristics	SERDES High-Speed Data Receiver section. Updated Table 3.26. Serial Input Data Specifications, Table 3.28. Receiver Total Jitter Tolerance Specification, and Table 3.29. External Reference Clock Specification (refclkp/refclkn).
			Modified section heading to XXAUI/CPRI LV E.30 Electrical and Timing Characteristics. Updated Table 3.33 Transmit and Table 3.34. Receive and Jitter Tolerance.
			Modified section heading to CPRI LV E.24 Electrical and Timing Characteristics. Updated Table 3.35. Transmit and Table 3.36. Receive and Jitter Tolerance.
			Modified section heading to Gigabit Ethernet/SGMII/CPRI LV E.12 Electrical and Timing Characteristics. Updated Table 3.37. Transmit and Table 3.38. Receive and Jitter Tolerance.
June 2014	1.1	Ordering Information	Updated ECP5/ECP5-5G Part Number Description and Ordering Part Numbers sections.
March 2014	1.0	All	Initial release.